Phase out

Standard Rectifier Module

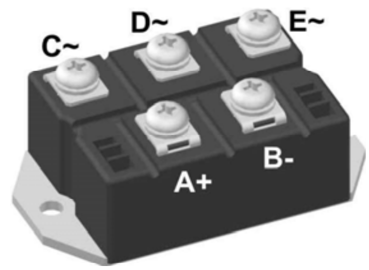
PHASE OUT

3~ Rectifier Bridge

3~ Rectifier		
V_{RRM}	=	1400 V
I_{DAV}	=	240 A
I_{FSM}	=	2800 A

Part number

VUO190-14NO7



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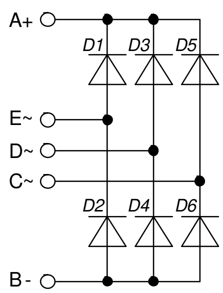


Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-E

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

Recommended replacement: VUO190-16NO7

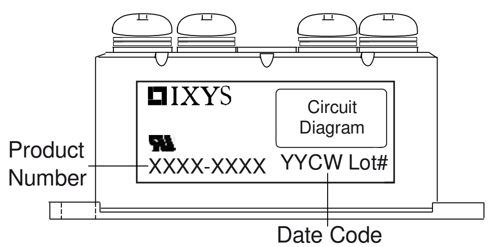
Rectifier

Symbol	Definition	Conditions		min.	typ.	max.	Unit
				Ratings			
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			1500	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			1400	V
I_R	*reverse current*	V_R = 1400 V	T_{VJ} = 25°C			200	µA
		V_R = 1400 V	T_{VJ} = 150°C			3.5	mA
V_F	*forward voltage drop*	I_F = 80 A	T_{VJ} = 25°C			1.07	V
		I_F = 240 A				1.36	V
		I_F = 80 A	T_{VJ} = 125°C			0.96	V
		I_F = 240 A				1.33	V
I_{DAV}	*bridge output current*	T_C = 110°C rectangular d = ⅓	T_{VJ} = 150°C			240	A
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.74	V
r_F	*slope resistance* } *for power loss calculation only*					2.4	mΩ
R_{thJC}	*thermal resistance junction to case*					0.4	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.15		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			310	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			2.80	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			3.03	kA
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			2.38	kA
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			2.57	kA
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			39.2	kA^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			38.1	kA^2s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			28.3	kA^2s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			27.5	kA^2s
C_J	*junction capacitance*	V_R = 400 V; f = 1 MHz	T_{VJ} = 25°C		133		pF

PHASE OUT

Phase out

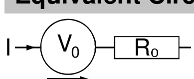
Package PWS-E			Ratings			
Symbol	**Definition**	**Conditions**	**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal			250	A
T_{VJ}	*virtual junction temperature*		-40		150	°C
T_{op}	*operation temperature*		-40		125	°C
T_{stg}	*storage temperature*		-40		125	°C
Weight				284		g
M_D	*mounting torque*		4.25		5.75	Nm
M_T	*terminal torque*		4.25		5.75	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*	*terminal to terminal*	12.0			mm
$d_{Spb/Apb}$		*terminal to backside*	26.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second; 50/60 Hz, RMS; $I_{ISOL} \le 1$ mA	3000			V
		t = 1 minute	2500			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO190-14NO7	VUO190-14NO7	Box	5	462500

Equivalent Circuits for Simulation

* *on die level* $T_{VJ} = 150\,°C$

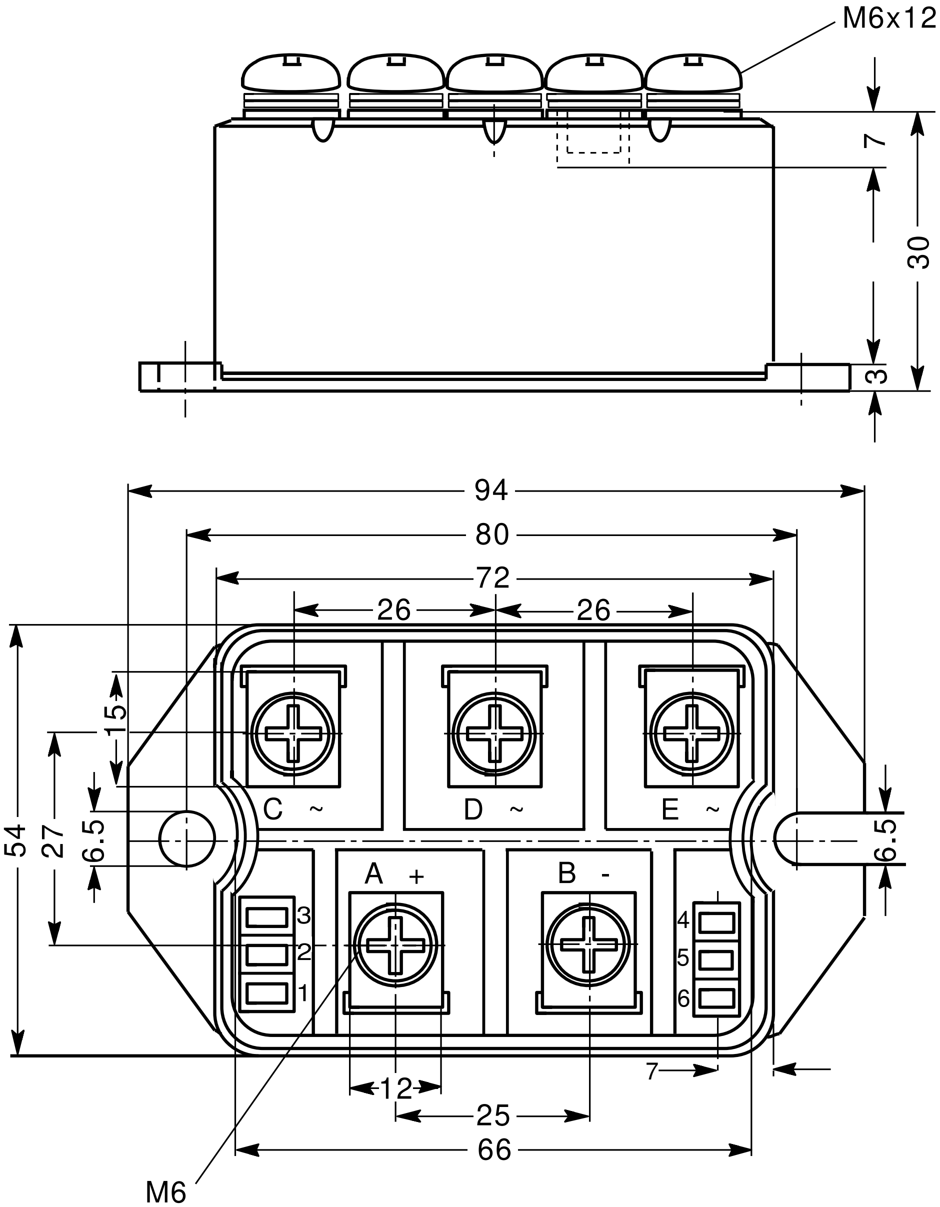


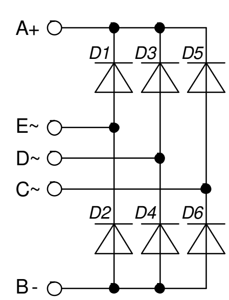
Rectifier

$V_{0\,max}$	*threshold voltage*	0.74	V
$R_{0\,max}$	*slope resistance **	1.2	mΩ

Phase out

Outlines PWS-E





Phase out

Rectifier

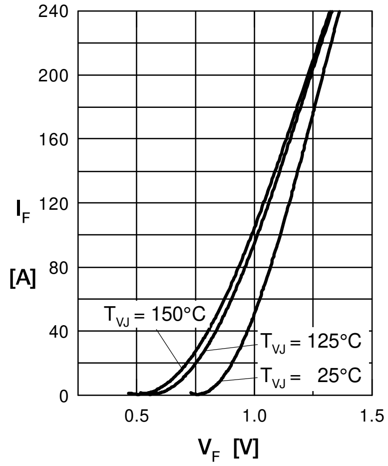


Fig. 1 Forward current vs. voltage drop per diode

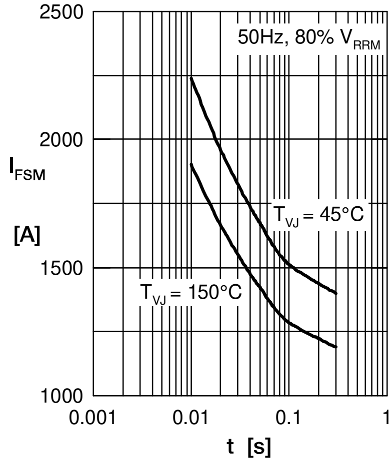


Fig. 2 Surge overload current vs. time per diode

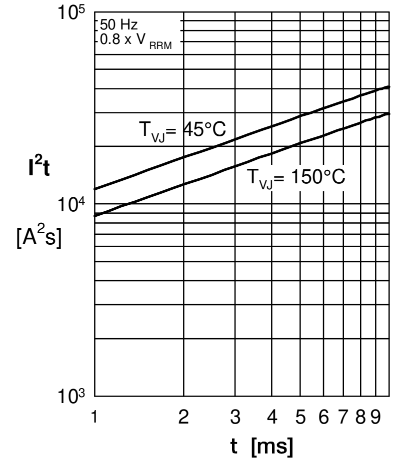


Fig. 3 I^2t vs. time per diode

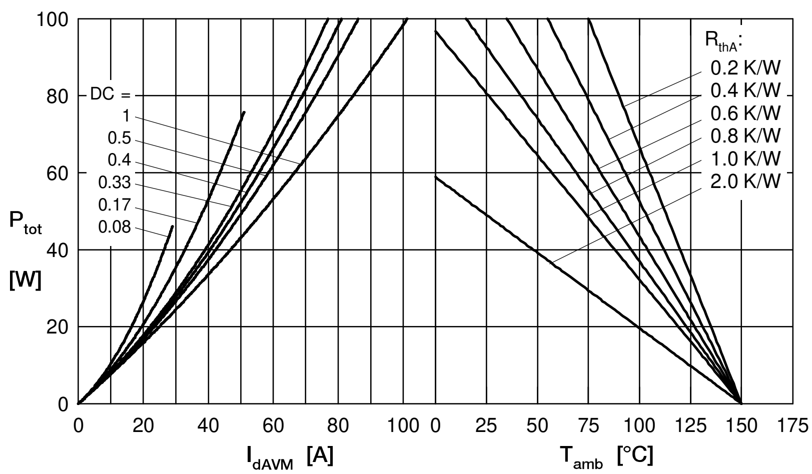


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

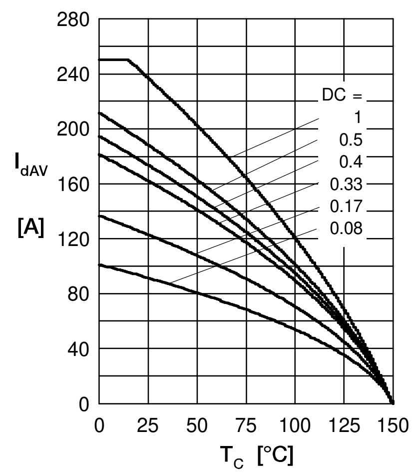


Fig. 5 Max. forward current vs. case temperature per diode

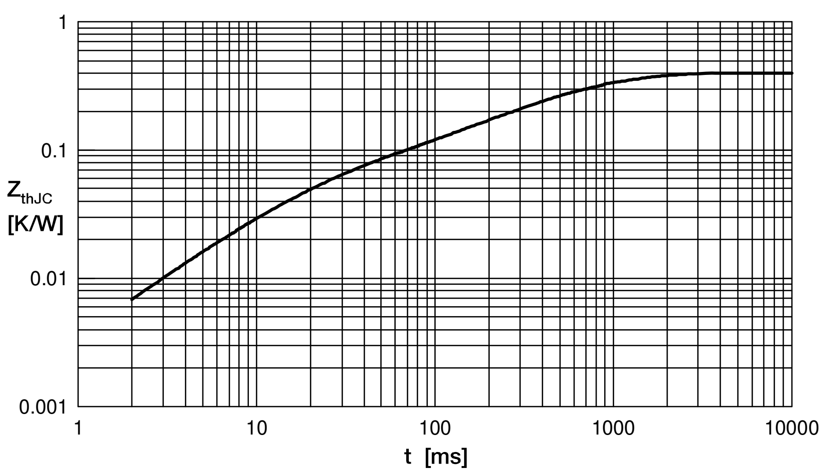


Fig. 6 Transient thermal impedance junction to case vs. time per diode

R_i	t_i
0.050	0.02
0.003	0.01
0.100	0.225
0.177	0.8
0.070	0.58